



# STH260N6F6-2

N-channel 60 V, 1.7 mΩ typ., 180 A STripFET™ VI DeepGATE™ Power MOSFET in H<sup>2</sup>PAK-2 package

Datasheet — production data

## Features

Order code	V <sub>DSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STH260N6F6-2	60 V	< 2.4 mΩ	180 A

- Low gate charge
- Very low on-resistance
- High avalanche ruggedness

## Applications

- Switching applications

## Description

This device is an N-channel Power MOSFET developed using the 6<sup>th</sup> generation of STripFET™ DeepGATE™ technology, with a new gate structure. The resulting Power MOSFET exhibits the lowest R<sub>DS(on)</sub> in all packages.

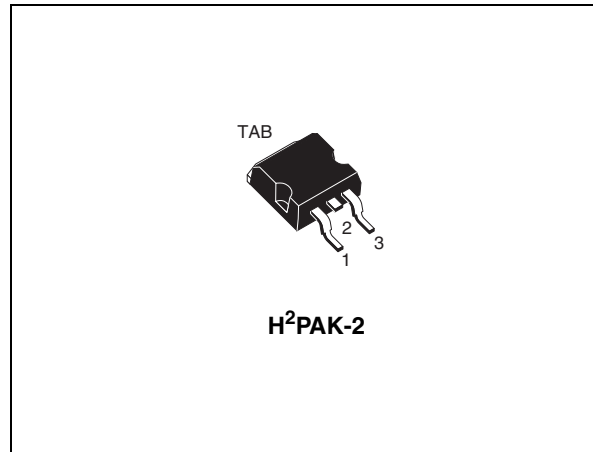


Figure 1. Internal schematic diagram

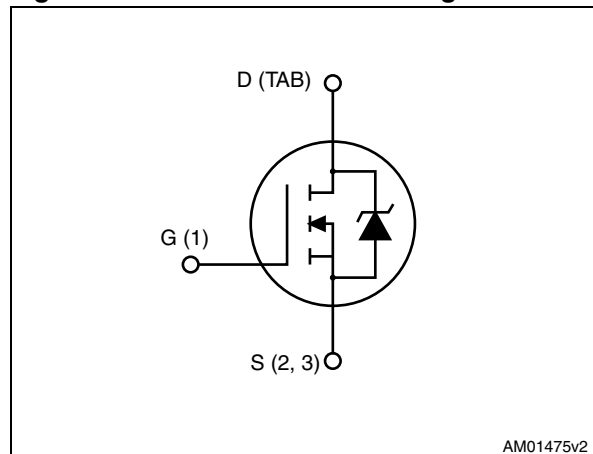


Table 1. Device summary

Order code	Marking	Package	Packaging
STH260N6F6-2	260N6F6	H <sup>2</sup> PAK-2	Tape and reel

# Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>3</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>4</b>
	2.1 Electrical characteristics (curves) .....	6
<b>3</b>	<b>Test circuits</b> .....	<b>8</b>
<b>4</b>	<b>Package mechanical data</b> .....	<b>9</b>
<b>5</b>	<b>Revision history</b> .....	<b>13</b>

# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	60	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	180	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	180	A
$I_{DM}^{(1)}$	Drain current (pulsed)	720	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	300	W
	Derating factor	2	W/ $^\circ\text{C}$
$T_{stg}$	Storage temperature	- 55 to 175	$^\circ\text{C}$
$T_j$	Operating junction temperature		

1. Current limited by package.

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.5	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	35	$^\circ\text{C}/\text{W}$
$T_l$	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

1. When mounted on FR-4 board of 1 inch<sup>2</sup>, 2 oz Cu.

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 4. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ( $V_{GS} = 0$ )	$I_D = 250\ \mu\text{A}$	60			V
$I_{DSS}$	Zero gate voltage Drain current ( $V_{GS} = 0$ )	$V_{DS} = 60\ \text{V}$ $V_{DS} = 60\ \text{V}, T_C = 125\text{ °C}$			1 100	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\ \text{V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\ \text{V}, I_D = 60\ \text{A}$		1.7	2.4	m $\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance			11800		pF
$C_{oss}$	Output capacitance	$V_{DS} = 25\ \text{V}, f = 1\ \text{MHz},$ $V_{GS} = 0$	-	1235	-	pF
$C_{rss}$	Reverse transfer capacitance			488		pF
$Q_g$	Total gate charge	$V_{DD} = 30\ \text{V}, I_D = 120\ \text{A},$ $V_{GS} = 10\ \text{V}$ <i>(see Figure 14)</i>		183		nC
$Q_{gs}$	Gate-source charge		-	53	-	nC
$Q_{gd}$	Gate-drain charge			41		nC

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 30\ \text{V}, I_D = 60\ \text{A}$ $R_G = 4.7\ \Omega, V_{GS} = 10\ \text{V}$ <i>(see Figure 13)</i>	-	31.4	-	ns
$t_r$	Rise time			165		
$t_{d(off)}$	Turn-off-delay time	<i>(see Figure 13)</i>	-	144.4	-	ns
$t_f$	Fall time			62.6		

**Table 7. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current				180	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				720	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 180 \text{ A}, V_{GS} = 0$			1.1	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 120 \text{ A}, V_{DD} = 48 \text{ V}$ $di/dt = 100 \text{ A}/\mu\text{s},$ $T_j = 150 \text{ }^\circ\text{C}$ <i>(see Figure 15)</i>	-	55.6		ns
$Q_{rr}$	Reverse recovery charge			116		nC
$I_{RRM}$	Reverse recovery current			3.8		A

1. Current limited by package.
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

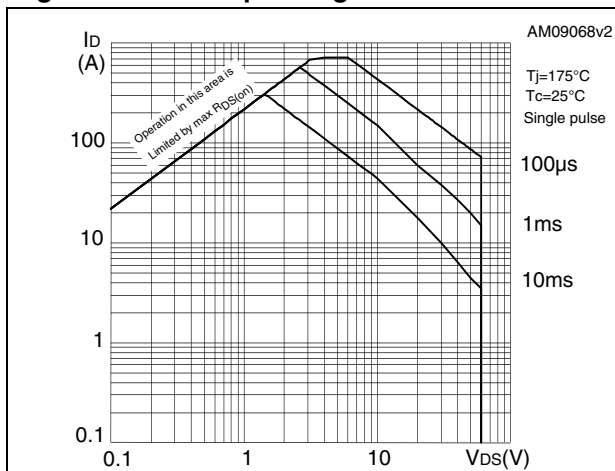


Figure 3. Thermal impedance

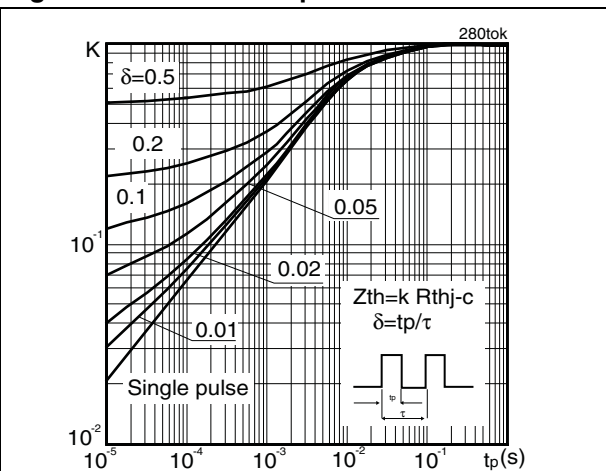


Figure 4. Output characteristics

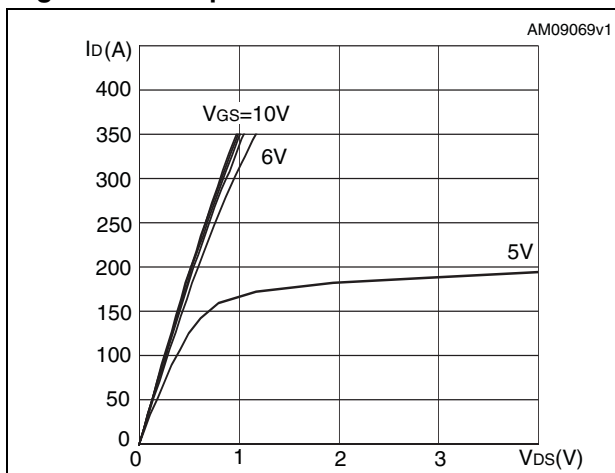


Figure 5. Transfer characteristics

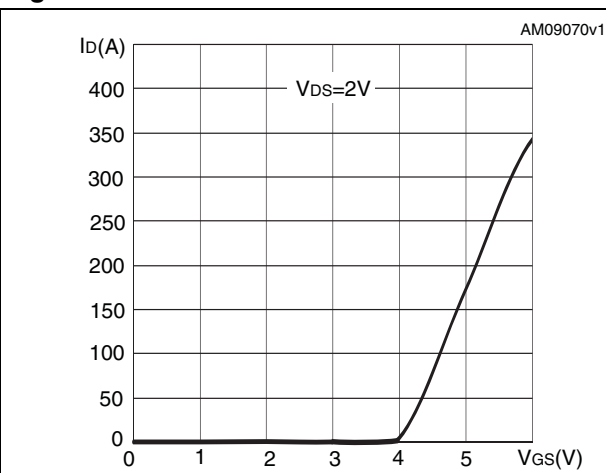


Figure 6. Normalized  $B_{V_{DSS}}$  vs. temperature

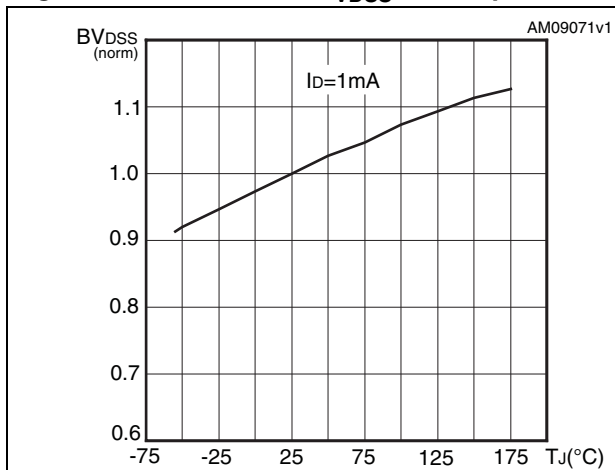
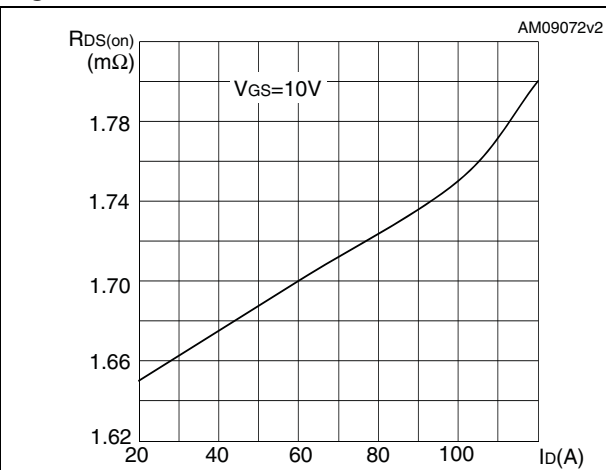
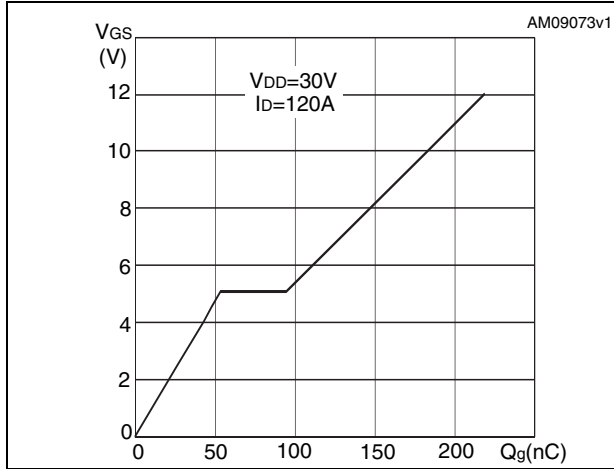


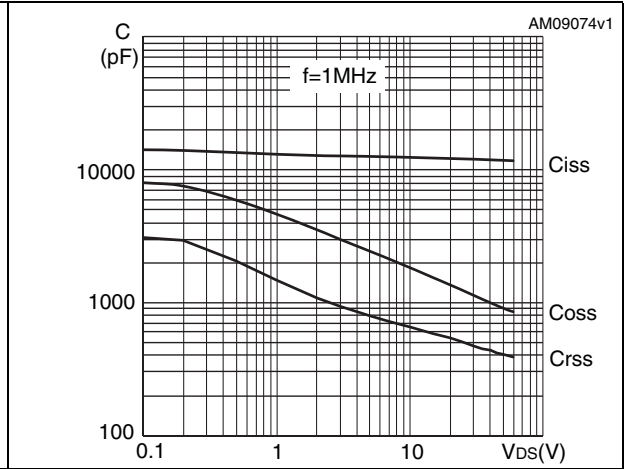
Figure 7. Static drain-source on-resistance



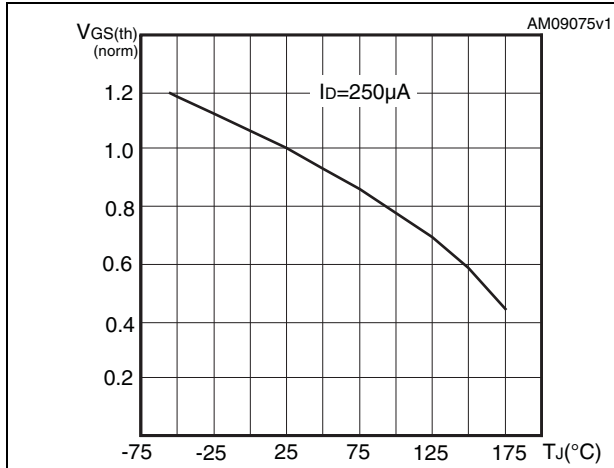
**Figure 8. Gate charge vs. gate-source voltage**



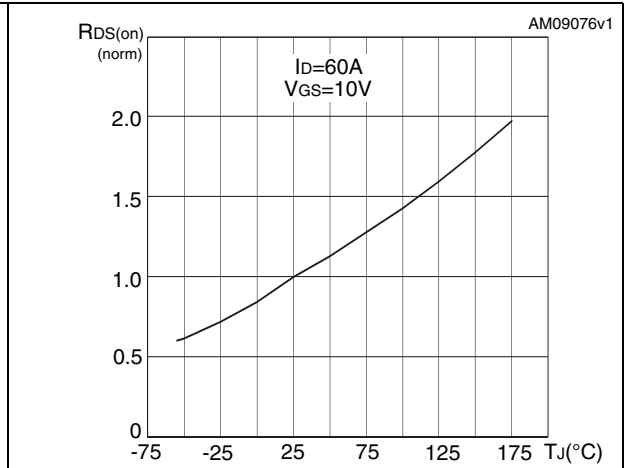
**Figure 9. Capacitance variations**



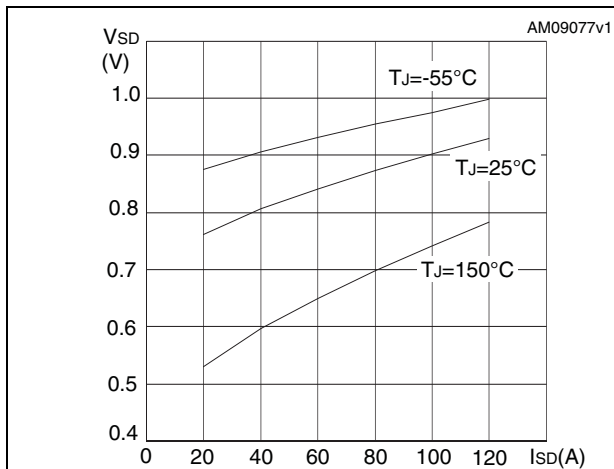
**Figure 10. Normalized gate threshold voltage vs. temperature**



**Figure 11. Normalized on-resistance vs. temperature**



**Figure 12. Source-drain diode forward characteristics**



### 3 Test circuits

**Figure 13. Switching times test circuit for resistive load**



AM01468v1

**Figure 14. Gate charge test circuit**



AM01469v1

**Figure 15. Test circuit for inductive load switching and diode recovery times**



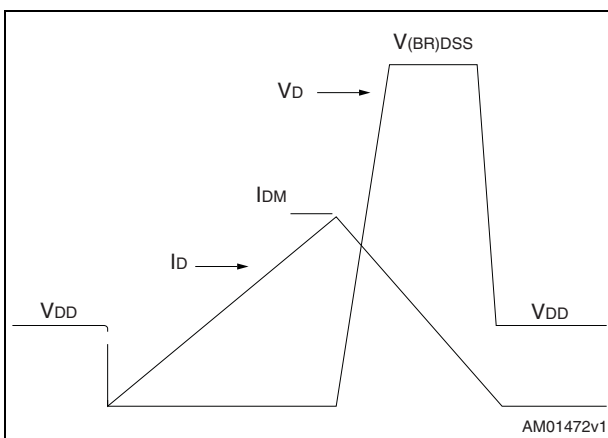
AM01470v1

**Figure 16. Unclamped inductive load test circuit**



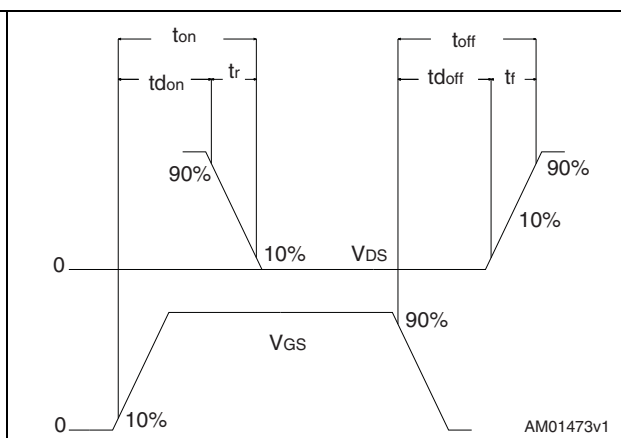
AM01471v1

**Figure 17. Unclamped inductive waveform**



AM01472v1

**Figure 18. Switching time waveform**



AM01473v1



## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

Table 8. H<sup>2</sup>PAK 2 leads mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.30		4.80
A1	0.03		0.20
C	1.17		1.37
e	4.98		5.18
E	0.50		0.90
F	0.78		0.85
H	10.00		10.40
H1	7.40		7.80
L	15.30		15.80
L1	1.27		1.40
L2	4.93		5.23
L3	6.85		7.25
L4	1.5		1.7
M	2.6		2.9
R	0.20		0.60
V	0°		8°

Figure 19. H<sup>2</sup>PAK 2 leads drawing

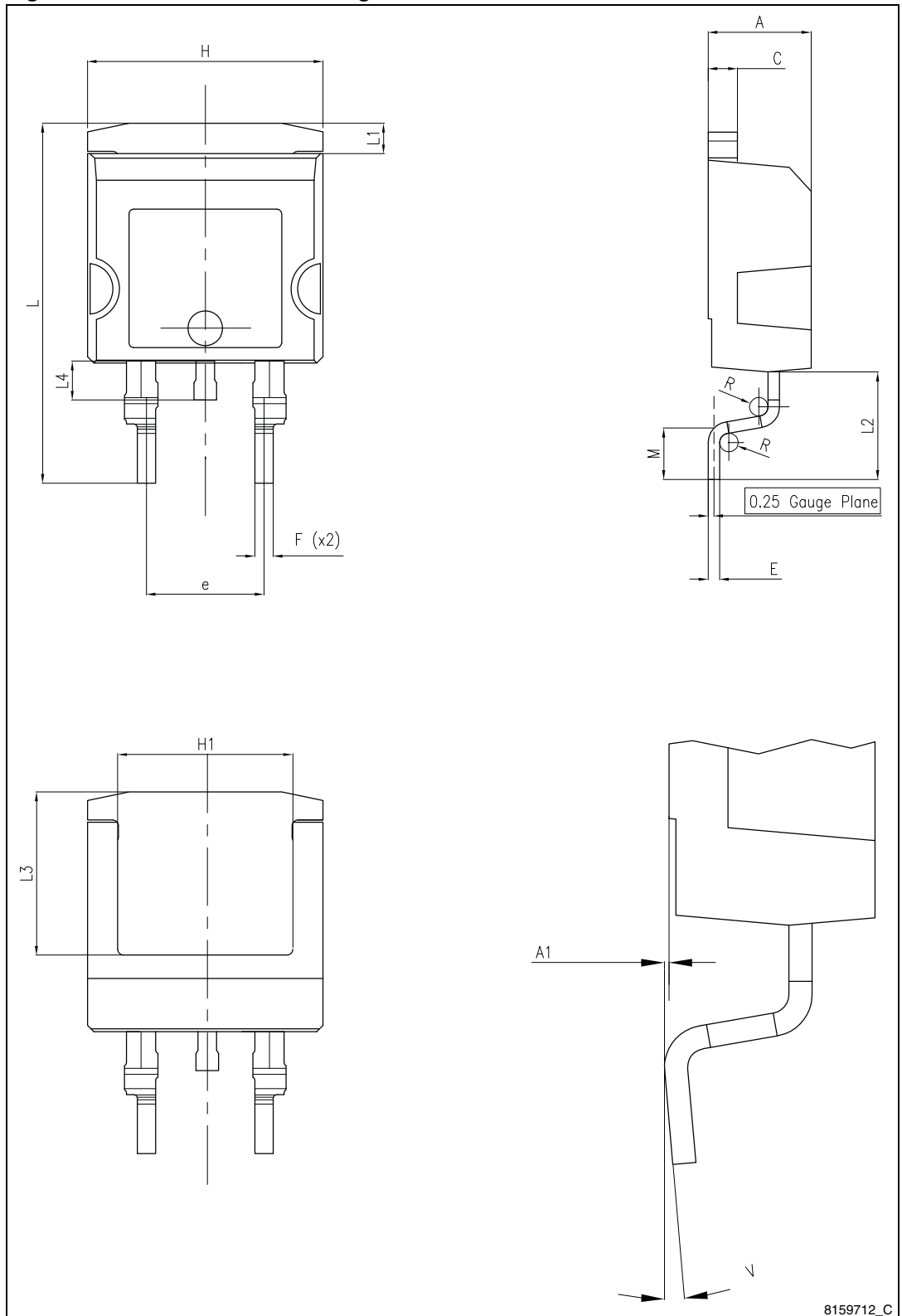
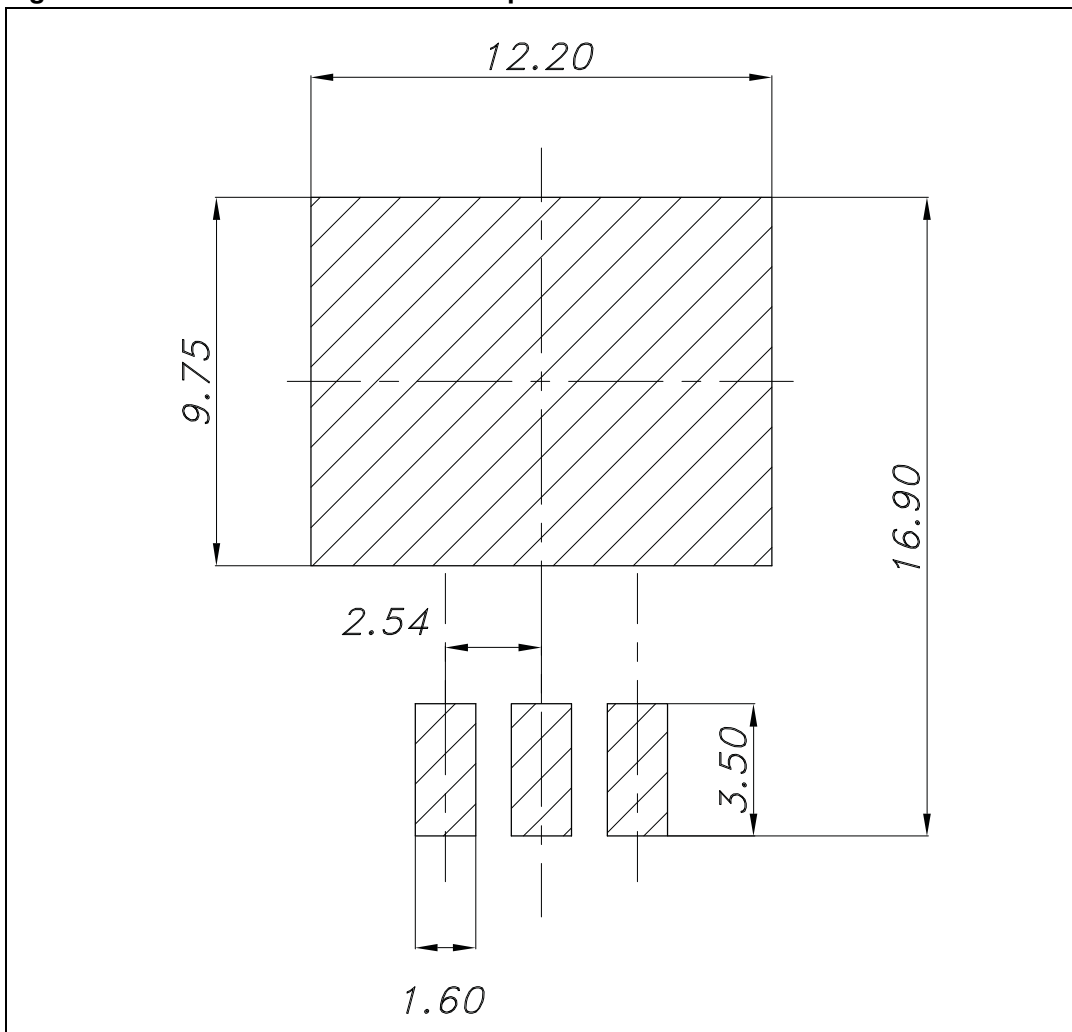


Figure 20. H<sup>2</sup>PAK 2 recommended footprint



## 5 Revision history

**Table 9. Document revision history**

Date	Revision	Changes
31-May-2011	1	First release.
25-Aug-2011	2	Updated mechanical data.
01-Feb-2012	3	Updated <i>Table 2: Absolute maximum ratings</i> . Minor text changes.
06-Jul-2012	4	<i>Section 2.1: Electrical characteristics (curves)</i> has been added.

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